

Features

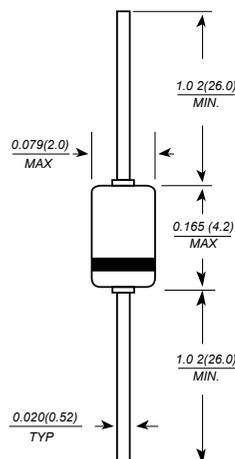
- For general purpose applications
- This diode features low turn-on voltage and high breakdown voltage. This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges

Mechanical Data

- Case: DO-35, glass case
- Polarity: Color band denotes cathode
- Weight: 0.004 ounces, 0.13 grams



DO-35(GLASS)



Dimensions in millimeters

Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Continuous reverse voltage	V_{RRM}	100	V
Forward continuous current @ $T_A=25^\circ\text{C}$	I_F	100 ¹⁾	mA
Repetitive peak forward current t_p 1s, 0.5	I_{FRM}	350 ¹⁾	mA
Surge forward current @ t_p 10ms	I_{FSM}	750 ¹⁾	mA
Power dissipation @ $T_A=95^\circ\text{C}$	P_{tot}	100 ¹⁾	mW
Junction temperature	T_J	-55 ----+ 125	$^\circ\text{C}$
Ambient operating temperature range	T_L	230	$^\circ\text{C}$
Storage temperature range	T_{STG}	-55 ----+ 150	$^\circ\text{C}$

1) On infinite heatsink with 4mm lead length.

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Reverse breakdown voltage @ $I_R=100\mu\text{A}, T_J=25^\circ\text{C}$	V_{BR}	100	-	-	V
Forward voltage @ $I_F=1\text{mA}, T_J=25^\circ\text{C}$	V_F	-	0.4	0.45	V
@ $I_F=200\text{mA}, T_J=25^\circ\text{C}$		-	-	1.0	
Leakage current @ $T_J=25^\circ\text{C}$	I_R	-	-	0.1	μA
$V_R=50\text{V}$ @ $T_J=100^\circ\text{C}$		-	-	20	
Junction capacitance at $V_R=1\text{V}, f=1\text{MHz}$	C_J	-	-	20	pF
Thermal resistance junction to ambient	$R_{\theta JA}$	-	-	300 ¹⁾	$^\circ\text{C/W}$

2) Pulse test $t_p < 300 \mu\text{s}$, $\delta < 2\%$



FIG.1 – ADMISSIBLE POWER DISSIPATION VS. AMBIENT TEMPERATURE

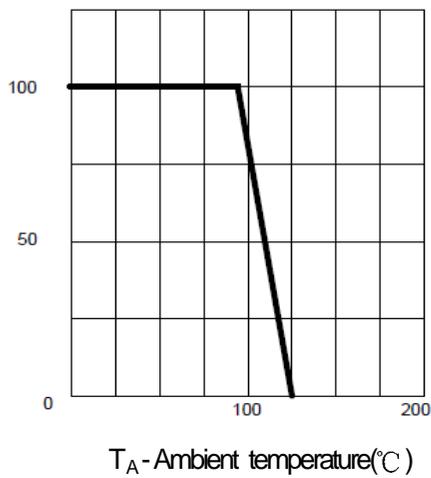


FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

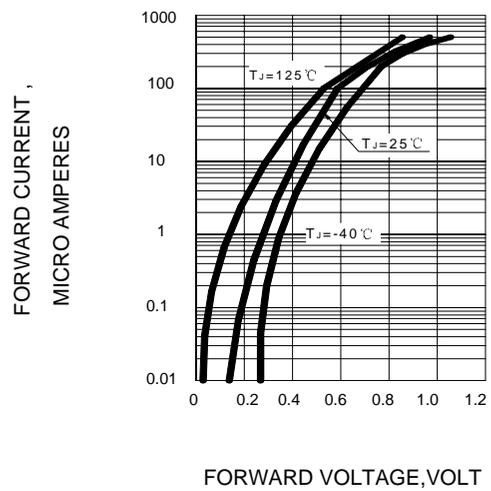


FIG.3 – TYPICAL REVERSE CHARACTERISTICS

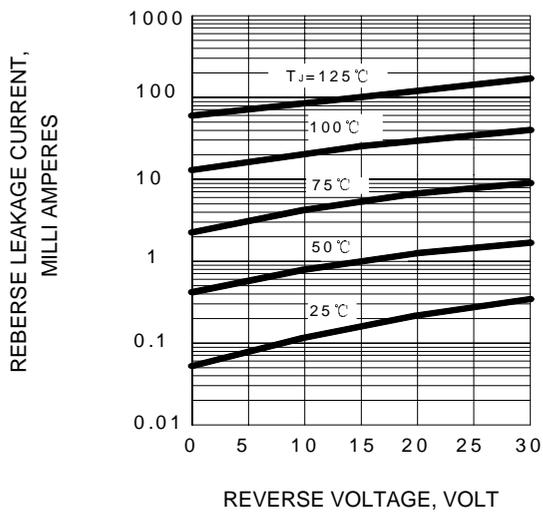


FIG.4 – TYPICAL JUNCTION CAPACITANCE

